SKM100GAL12F4

SEMITRANS® 2

High Speed IGBT4 Modules

SKM100GAL12F4

Features*

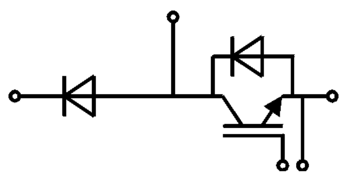
- High speed trench and field-stop IGBT
- CAL4 ultra-fast = soft switching 4. generation CAL-diode
- Insulated copper baseplate using DBC technology (Direct Bonded Copper)
- Increased power cycling capability
- For higher switching frequencies above 15kHz
- UL recognized, file no. E63532

Typical Applications

- Electronic welders
- DC/DC – converter
- Brake chopper
- Switched reluctance motor

Remarks

- Case temperature limited to T_c = 125°C max.
- Recommended T_{op} = -40 ... +150°C
- Product reliability results valid for T_j = 150°C



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Absolute Maximum Ratings				
Symbol	**Conditions**		**Values**	**Unit**
IGBT				
V_{CES}	T_j = 25 °C		1200	V
I_C	T_j = 175 °C	T_c = 25 °C	153	A
		T_c = 80 °C	117	A
I_{Cnom}			100	A
I_{CRM}	I_{CRM} = 2 x I_{Cnom}		200	A
V_{GES}			-20 ... 20	V
t_{psc}	V_{CC} = 800 V $V_{GE} \leq$ 15 V $V_{CES} \leq$ 1200 V	T_j = 150 °C	10	µs
T_j			-40 ... 175	°C
Inverse diode				
V_{RRM}	T_j = 25 °C		1200	V
I_F	T_j = 175 °C	T_c = 25 °C	111	A
		T_c = 80 °C	82	A
I_{Fnom}			100	A
I_{FRM}	I_{FRM} = 2xI_{Fnom}		200	A
I_{FSM}	t_p = 10 ms, sin 180°, T_j = 25 °C		550	A
T_j			-40 ... 175	°C
Freewheeling diode				
V_{RRM}	T_j = 25 °C		1200	V
I_F	T_j = 175 °C	T_c = 25 °C	111	A
		T_c = 80 °C	82	A
I_{Fnom}			100	A
I_{FRM}	I_{FRM} = 2xI_{Fnom}		200	A
I_{FSM}	t_p = 10 ms, sin 180°, T_j = 25 °C		550	A
T_j			-40 ... 175	°C
Module				
$I_{t(RMS)}$			200	A
T_{stg}	module without TIM		-40 ... 125	°C
V_{isol}	AC sinus 50 Hz, t = 1 min		4000	V

Characteristics						
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Unit**
IGBT						
$V_{CE(sat)}$	I_C = 100 A V_{GE} = 15 V chiplevel	T_j = 25 °C		2.05	2.38	V
		T_j = 150 °C		2.55	2.93	V
V_{CE0}	chiplevel	T_j = 25 °C		1.10	1.28	V
		T_j = 150 °C		0.95	1.13	V
r_{CE}	V_{GE} = 15 V chiplevel	T_j = 25 °C		9.5	11	mΩ
		T_j = 150 °C		16	18	mΩ
$V_{GE(th)}$	V_{GE}=V_{CE}, I_C = 3.8 mA		5.1	5.8	6.4	V
I_{CES}	V_{GE} = 0 V V_{CE} = 1200 V	T_j = 25 °C			1	mA
		T_j = 150 °C		-		mA
C_{ies}	V_{CE} = 25 V V_{GE} = 0 V	f = 1 MHz		6.2		nF
C_{oes}		f = 1 MHz		0.41		nF
C_{res}		f = 1 MHz		0.35		nF
Q_G	V_{GE} = - 8 V...+ 15 V			567		nC
R_{Gint}	T_j = 25 °C			0		Ω

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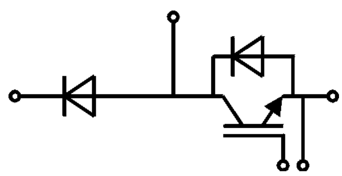

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Characteristics						
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Unit**
$t_{d(on)}$	V_{CC} = 600 V	T_j = 150 °C		12		ns
t_r	I_C = 100 A	T_j = 150 °C		20		ns
E_{on}	V_{GE} = +15/-15 V $R_{G\ on}$ = 3.9 Ω	T_j = 150 °C		6.6		mJ
$t_{d(off)}$	$R_{G\ off}$ = 3.9 Ω	T_j = 150 °C		315		ns
t_f	di/dt_{on} = 5000 A/µs	T_j = 150 °C		65		ns
E_{off}	di/dt_{off} = 1300 A/µs dv/dt = 4300 V/µs L_s = 26 nH	T_j = 150 °C		8		mJ
$R_{th(j-c)}$	per IGBT				0.238	K/W
$R_{th(c-s)}$	per IGBT (λ_{grease}=0.81 W/(m*K))			0.122		K/W
Inverse diode						
$V_F = V_{EC}$	I_F = 100 A	T_j = 25 °C		2.55	2.93	V
	V_{GE} = 0 V chiplevel	T_j = 150 °C		2.46	2.80	V
V_{F0}	chiplevel	T_j = 25 °C		1.51	1.75	V
		T_j = 150 °C		1.16	1.40	V
r_F	chiplevel	T_j = 25 °C		10	12	mΩ
		T_j = 150 °C		13	14	mΩ
I_{RRM}	I_F = 100 A	T_j = 150 °C		200		A
Q_{rr}	di/dt_{off} = 5000 A/µs	T_j = 150 °C		16.5		µC
E_{rr}	V_{GE} = -15 V V_{CC} = 600 V	T_j = 150 °C		6.3		mJ
$R_{th(j-c)}$	per diode				0.483	K/W
$R_{th(c-s)}$	per diode (λ_{grease}=0.81 W/(m*K))			0.134		K/W
Freewheeling diode						
$V_F = V_{EC}$	I_F = 100 A	T_j = 25 °C		2.55	2.93	V
	V_{GE} = 0 V chiplevel	T_j = 150 °C		2.46	2.80	V
V_{F0}	chiplevel	T_j = 25 °C		1.51	1.75	V
		T_j = 150 °C		1.16	1.40	V
r_F	chiplevel	T_j = 25 °C		10	12	mΩ
		T_j = 150 °C		13	14	mΩ
I_{RRM}	I_F = 100 A	T_j = 150 °C		200		A
Q_{rr}	di/dt_{off} = 5000 A/µs	T_j = 150 °C		16.5		µC
E_{rr}	V_{GE} = -15 V V_{CC} = 600 V	T_j = 150 °C		6.3		mJ
$R_{th(j-c)}$	per diode				0.483	K/W
$R_{th(c-s)}$	per diode (λ_{grease}=0.81 W/(m*K))			0.134		K/W
Module						
L_{CE}				30		nH
$R_{CC'+EE'}$	measured per	T_C = 25 °C		0.65		mΩ
	switch	T_C = 125 °C		1.09		mΩ
$R_{th(c-s)1}$	calculated without thermal coupling (λ_{grease}=0.81 W/(m*K))			0.0639		K/W
$R_{th(c-s)2}$	including thermal coupling, T_s underneath module (λ_{grease}=0.81 W/(m*K))			0.071		K/W
M_s	to heat sink M6		3		5	Nm
M_t		to terminals M5	2.5		5	Nm
						Nm
w					160	g

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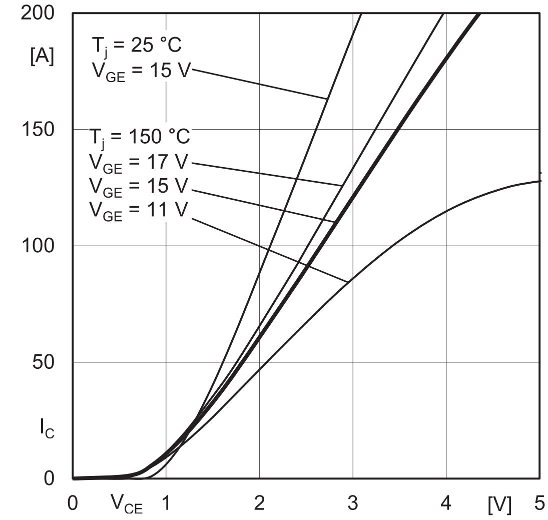


Fig. 1: Typ. output characteristic, inclusive $R_{CC'+EE'}$

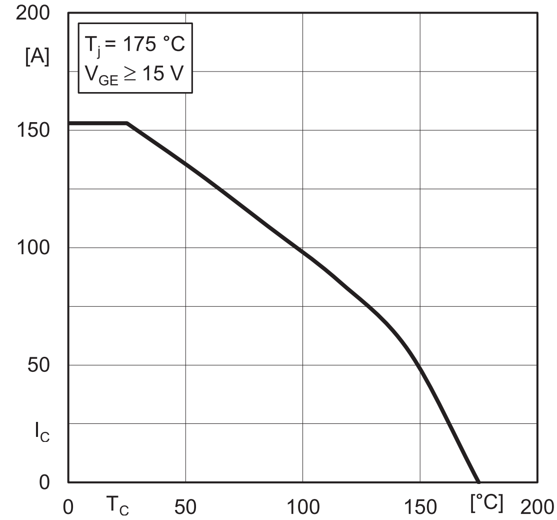


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

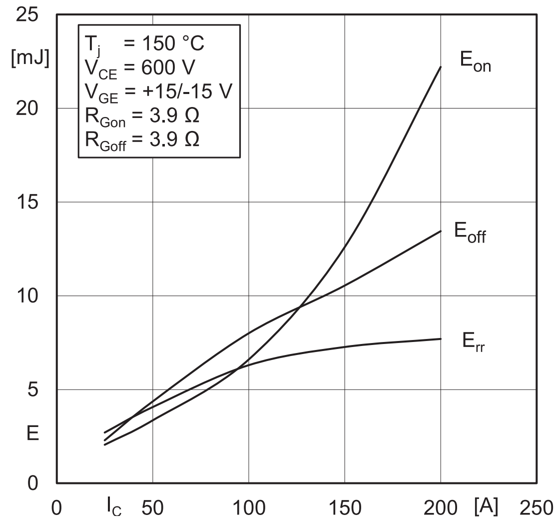


Fig. 3: Typ. turn-on /-off energy = f (I_C)

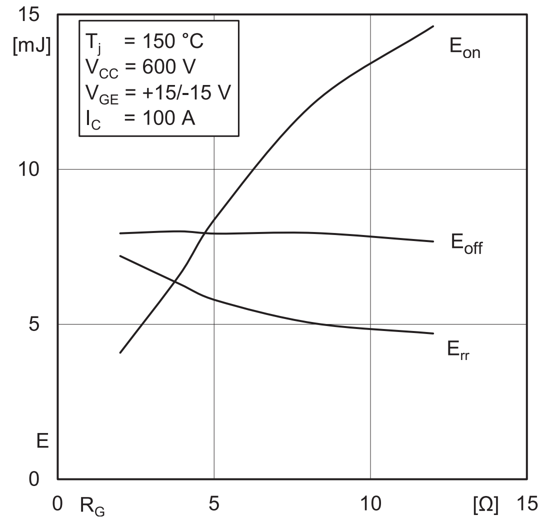


Fig. 4: Typ. turn-on /-off energy = f (R_G)

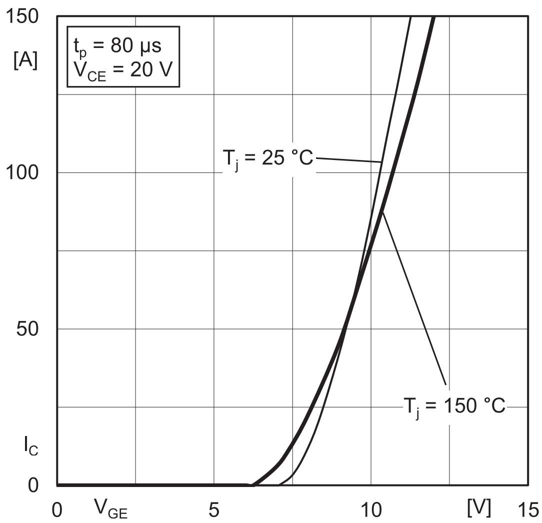


Fig. 5: Typ. transfer characteristic

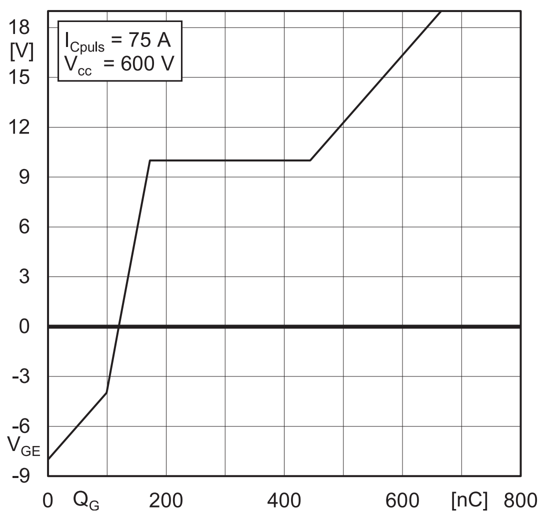


Fig. 6: Typ. gate charge characteristic

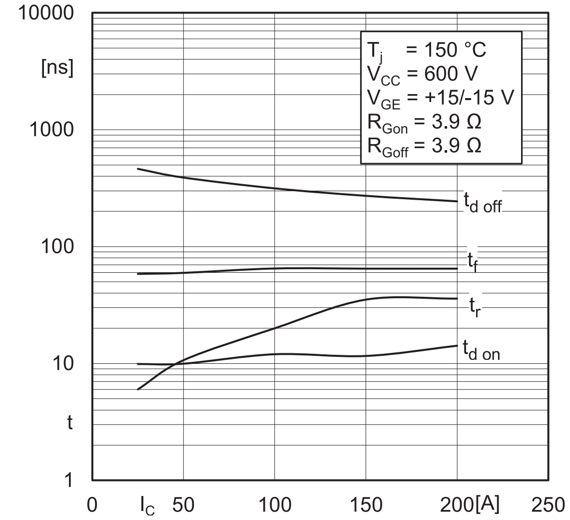


Fig. 7: Typ. switching times vs. I_C

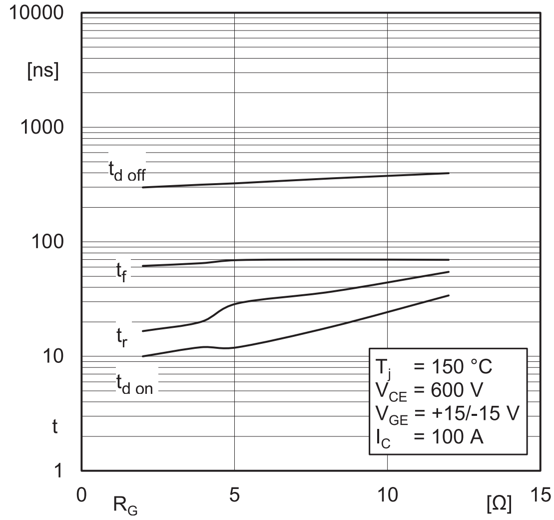


Fig. 8: Typ. switching times vs. gate resistor R_G

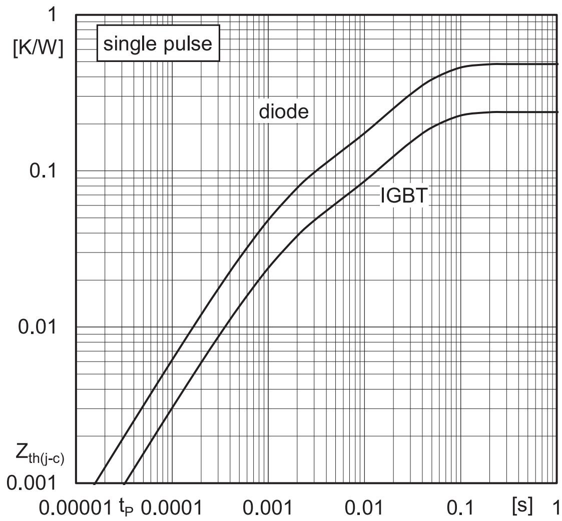


Fig. 9: Transient thermal impedance

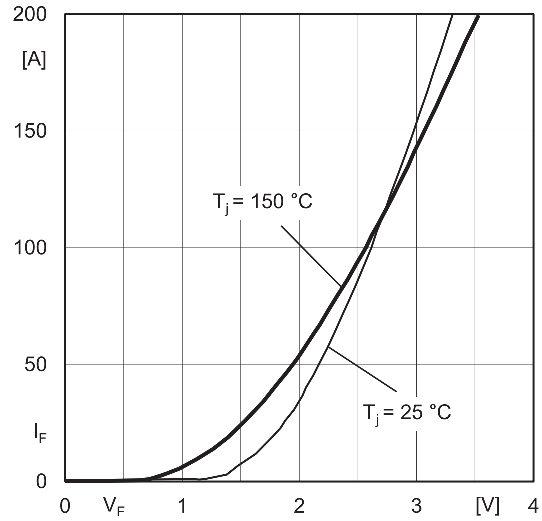


Fig. 10: Typ. CAL diode forward charact., incl. $R_{CC'+EE'}$

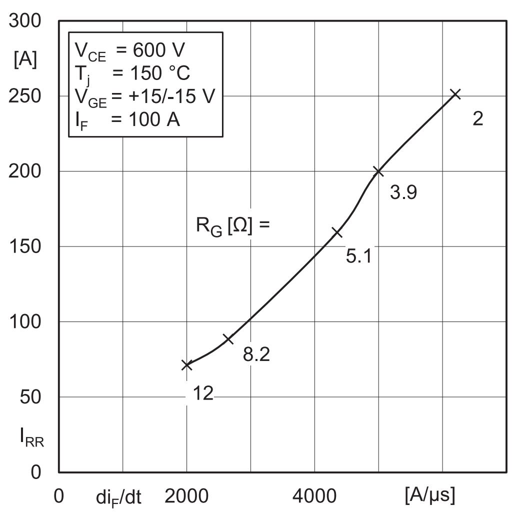


Fig. 11: Typ. CAL diode peak reverse recovery current

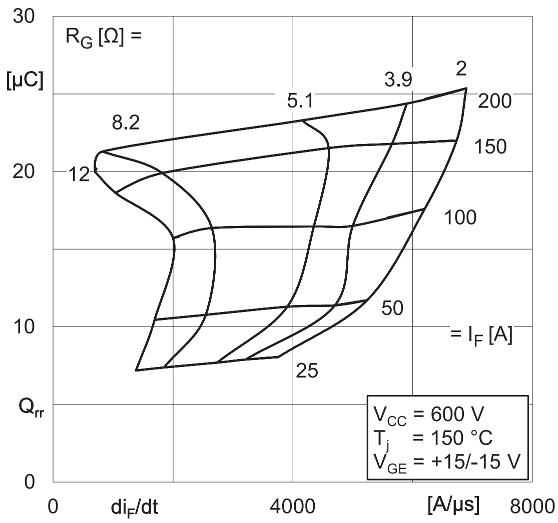
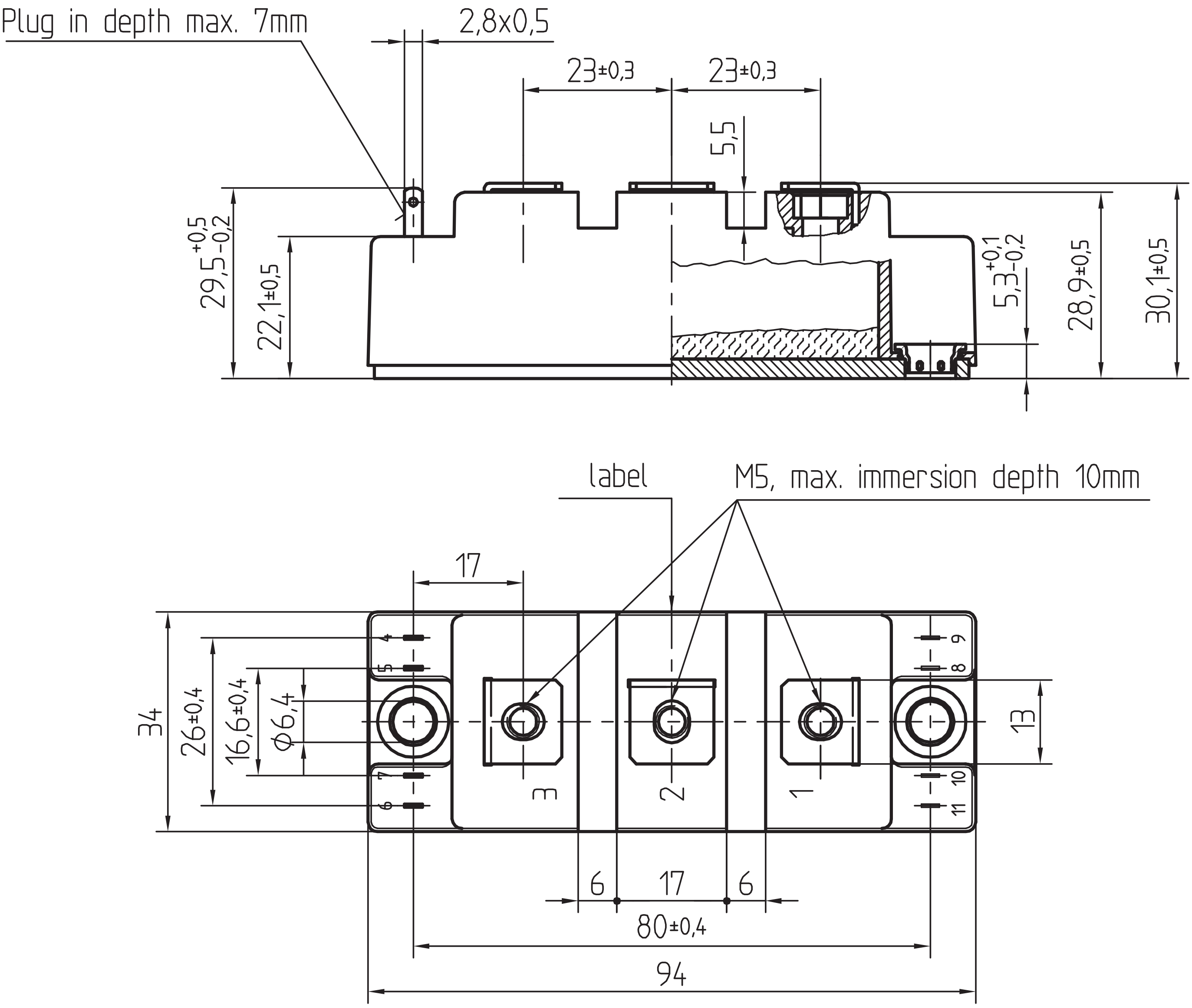


Fig. 12: Typ. CAL diode peak reverse recovery charge

Dimensions in mm



General tolerance +/- 0,5 mm

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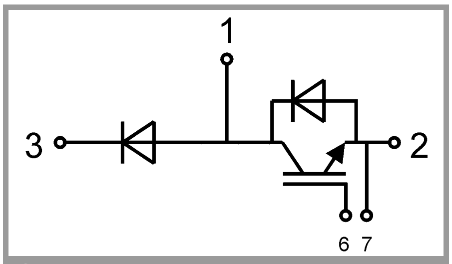

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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

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